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Vishay Siliconix

Automotive P-Channel 60 V (D-S) MOSFET



Marking Code: 9D

PRODUCT SUMMARY				
V _{DS} (V)	-60			
$R_{DS(on)}$ (Ω) at $V_{GS} = -10 \text{ V}$	0.290			
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5 \text{ V}$	0.395			
I _D (A)	-1.6			
Configuration	Single			
Package	SC-70			

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Typical ESD protection: 800 V
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ROHS COMPLIANT HALOGEN FREE

	(1, 2, 5, 6) D
(3) G O	
P-Channel MOSFET	
	(4) S

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unles	s otherwise noted	(k		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	-60	V	
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current	T _C = 25 °C a	1	-1.6		
Continuous drain current	T _C = 125 °C		-1		
Continuous source current (diode conduction) ^a		I _S	-1.6	Α	
Pulsed drain current ^b		I _{DM}	-6.7		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-8		
Single pulse avalanche energy	L = 0.1 MH	E _{AS}	3.2	mJ	
Maximum power dissipation ^b	T _C = 25 °C	р	2.7	W	
	T _C = 125 °C	P_{D}	0.5	VV	
Operating junction and storage temperature	range	T _J , T _{stg}	-55 to +150	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient P	PCB mount c	R_{thJA}	125	°C/W
Junction-to-foot (drain)		R _{thJF}	45	C/VV

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static		•						
Drain-source breakdown voltage	V _{DS}	V _{GS} =	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-1.5	-2.0	-2.5	V	
Cata assuma laglanda	_	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$		-	± 5	μΑ	
Gate-source leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 5	mA	
		V _{GS} = 0 V	V _{DS} = -60 V	-	-	-1		
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -60 V, T _J = 125 °C	-	-	-50	μΑ	
		V _{GS} = 0 V	V _{DS} = -60 V, T _J = 150 °C	-	-	-150	1	
On-state drain current a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 V$	-5	-	-	Α	
Drain-source on-state resistance ^a		V _{GS} = -10 V	I _D = -2 A	-	0.230	0.290	Ω	
	_B	V _{GS} = -10 V	$I_D = -2 \text{ A}, T_J = 125 ^{\circ}\text{C}$	-	-	0.470		
	R _{DS(on)}	V _{GS} = -10 V	$I_D = -2 \text{ A}, T_J = 150 ^{\circ}\text{C}$	-	-	0.566		
		V _{GS} = -4.5 V	I _D = -1 A	-	0.305	0.395		
Forward transconductance b	9 _{fs}	V _{DS} =	-10 V, I _D = -1.5 A	-	3	-	S	
Dynamic ^b								
Input capacitance	C _{iss}			-	284	355		
Output capacitance	Coss	V _{GS} = 0 V V _{DS} = -25 V, f = 1 MHz		1	36	45	рF	
Reverse transfer capacitance	C _{rss}			-	28	35	1	
Total gate charge ^c	Qg			-	3.6	5.4		
Gate-source charge ^c	Q _{gs}	$V_{GS} = -4.5 \text{ V}$	$V_{GS} = -4.5 \text{ V}$ $V_{DS} = -30 \text{ V}, I_D = -1 \text{ A}$		1.2	-	nC	
Gate-drain charge ^c	Q_{gd}			-	1.7	-]	
Gate resistance	R _g		f = 1 MHz		6.05	9	Ω	
Turn-on delay time ^c	t _{d(on)}			-	44	66		
Rise time ^c	t _r	V_{DD} = -30 V, R_L = 30 Ω $I_D \cong$ -1 A, V_{GEN} = -4.5 V, R_g = 1 Ω		-	25	38		
Turn-off delay time ^c	t _{d(off)}			-	13	20	- ns	
Fall time ^c	t _f			-	9	14		
Source-Drain Diode Ratings and Char-	acteristics ^b							
Pulsed current ^a	I _{SM}			-	-	-6.7	Α	
Forward voltage	V _{SD}	I _F =	-0.5 A, V _{GS} = 0 V	-	-0.8	-1.2	V	

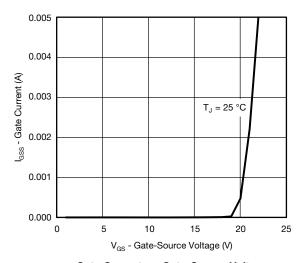
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

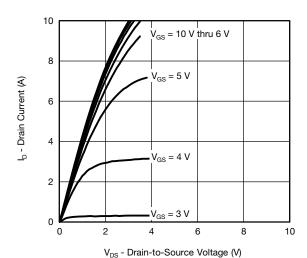
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



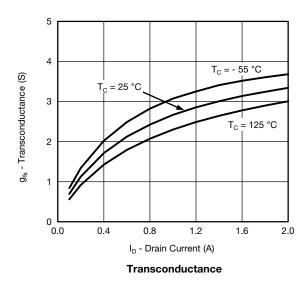
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

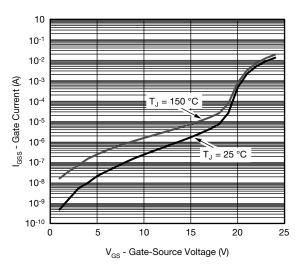


Gate Current vs. Gate-Source Voltage

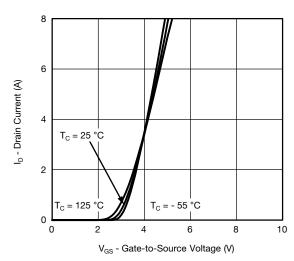


Output Characteristics

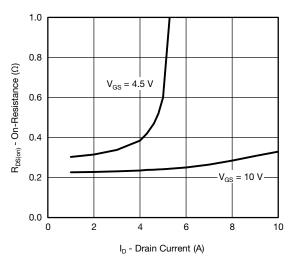




Gate Current vs. Gate-Source Voltage



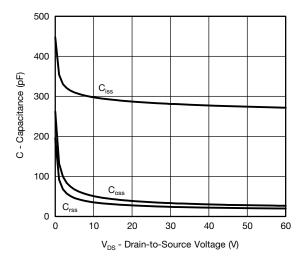
Transfer Characteristics



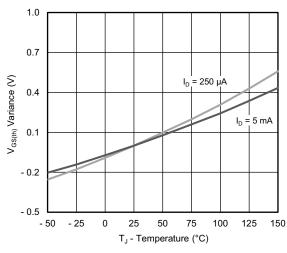
On-Resistance vs. Drain Current



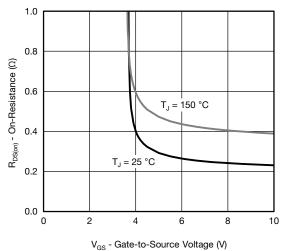
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



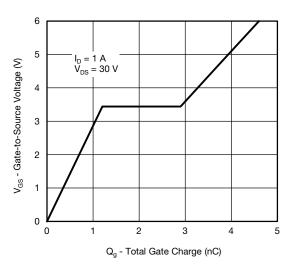
Capacitance



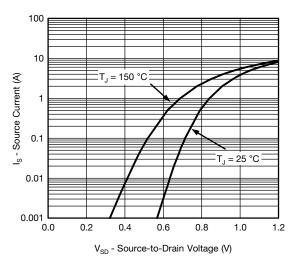
Threshold Voltage



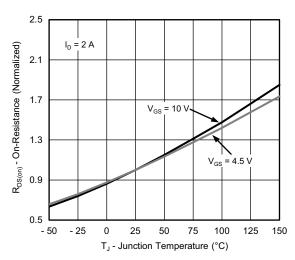
On-Resistance vs. Gate-to-Source Voltage



Gate Charge



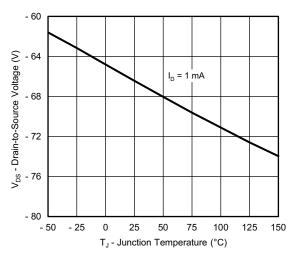
Source Drain Diode Forward Voltage



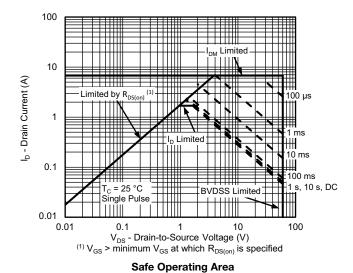
On-Resistance vs. Junction Temperature



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

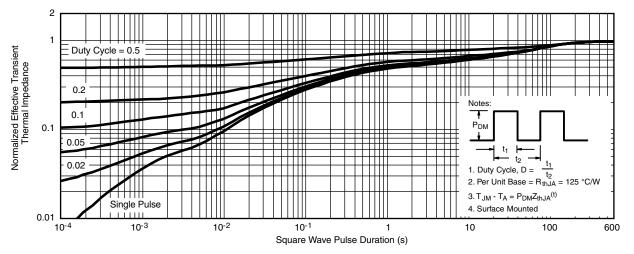


Drain Source Breakdown vs. Junction Temperature

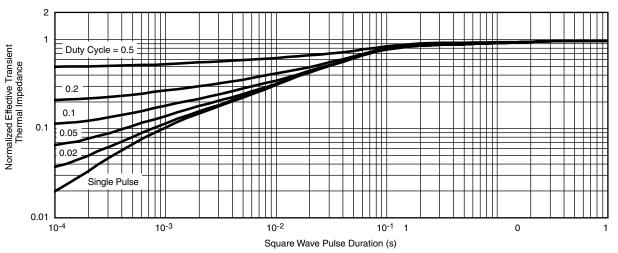




THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68494.





Vishay Siliconix

SC-70

Ordering codes for the SQ rugged series power MOSFETs in the SC-70 package:

DATASHEET PART NUMBER	OLD ORDERING CODE ^a	NEW ORDERING CODE
SQ1421EDH	-	SQ1421EDH-T1_GE3
SQ1431EH	SQ1431EH-T1-GE3	SQ1431EH-T1_GE3
SQ1440EH	-	SQ1440EH-T1_GE3
SQ1470AEH	-	SQ1470AEH-T1_GE3
SQ1539EH	-	SQ1539EH-T1_GE3
SQ1563AEH	-	SQ1563AEH-T1_GE3
SQ1902AEL	-	SQ1902AEL-T1_GE3
SQ1912AEEH	-	SQ1912AEEH-T1_GE3
SQ1912EH	-	SQ1912EH-T1_GE3

Note

a. Old ordering code is obsolete and no longer valid for new orders





SC-70: 6-LEADS





	MIL	LIMET	ERS	INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.90	-	1.10	0.035	_	0.043
A ₁	-	-	0.10	-	-	0.004
A_2	0.80	-	1.00	0.031	-	0.039
b	0.15	-	0.30	0.006	_	0.012
С	0.10	-	0.25	0.004	_	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
Ε	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
е		0.65BSC			0.026BSC	;
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
9	7°Nom				7°Nom	



RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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